

a side wall formed on a side surface of said gate electrode so as to be covered behind a visor portion of said gate electrode as seen in plan view; and  
an interlayer insulation film covering said gate electrode and being in contact with said side wall.

2. (Amended) A semiconductor device comprising:

a semiconductor substrate;  
a gate insulation film formed on said semiconductor substrate;  
a gate electrode formed on said gate insulation film and having a portion increasing upward in the length along a gate length direction, said gate electrode further having a visor portion;  
a side wall formed on a side surface of said gate electrode so as to be covered behind a visor portion of said gate electrode as seen in plan view;  
an interlayer insulation film covering said gate electrode; and  
a contact formed in said interlayer insulation film and being in contact with said side wall.

3. (Amended) A semiconductor device comprising:

a semiconductor substrate;  
a gate insulation film formed on said semiconductor substrate;  
a gate electrode formed on said gate insulation film and having a portion increasing upward in the length along a gate length direction, said gate electrode further having a visor portion; and

HAYES SOLOWAY P.C.  
130 W. CUSHING ST.  
TUCSON, AZ 85701  
TEL. 520.882.7623  
FAX. 520.882.7643

175 CANAL STREET  
MANCHESTER, NH 03101  
TEL. 603.668.1400  
FAX. 603.668.8567

a' a side wall formed on a side surface of said gate electrode so as to be covered behind a visor portion of said gate electrode as seen in plan view, said side wall being formed of a lamination of at least two insulation films having different etching properties.

Sub C1 7. (Amended) The semiconductor device according to claim 4, wherein the width of said visor portion is substantially constant and greater in length along said gate length direction than said upper or lower parts.

Q2 8. (Amended) The semiconductor device according to claim 5, wherein the width of said visor portion is substantially constant and greater in length along said gate length direction than said upper or lower parts.

9. (Amended) The semiconductor device according to claim 6, wherein the width of said visor portion is substantially constant and greater in length along said gate length direction than said upper or lower parts.

Sub B2 93 11. (Amended) The semiconductor device according to claim 4, wherein said side wall is formed on both a side surface of said upper part and a side surface of said lower part and is formed out of at least two different insulation films.

12. (Amended) The semiconductor device according to claim 5, wherein said side wall is formed on both a side surface of said upper part and a side surface of said lower part and is formed out of at least two different insulation films.

13. (Amended) The semiconductor device according to claim 6, wherein said side wall is formed on both a side surface of said upper part and a side surface of said lower part and is formed out of at least two different insulation films.

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175 CANAL STREET  
MANCHESTER, NH 03101  
TEL. 603.668.1400  
FAX. 603.668.8567